

Data Sheet July 1999 File Number 4763

Radiation Hardened Quad D-Type Flip-Flop with Reset

The Radiation Hardened ACS175MS is a Quad D-Type Flip-Flop with Reset. Information at the D input is transferred to the Q and \overline{Q} outputs on the positive-going transition of the clock. All four flip-flops are controlled by a common clock (CP) and a common reset (\overline{MR}). Resetting is accomplished by a LOW level independent of the clock. All inputs are buffered and the outputs are designed for balanced propagation delay and transition times.

The ACS175MS is fabricated on a CMOS Silicon on Sapphire (SOS) process, which provides an immunity to Single Event Latch-up and the capability of highly reliable performance in any radiation environment. These devices offer significant power reduction and faster performance when compared to ALSTTL types.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed below must be used when ordering.

Detailed Electrical Specifications for the ACS175MS are contained in SMD 5962-98635. A "hot-link" is provided on our homepage for downloading. http://www.intersil.com/spacedefense/spaceselect.htm

Features

- QML Qualified Per MIL-PRF-38535 Requirements
- 1.25 Micron Radiation Hardened SOS CMOS
- Radiation Environment
 - Latch-Up Free Under Any Conditions

 - SEU LET Threshold > 100MeV/(mg/cm²)
- Input Logic Levels. . . . $V_{IL} = (0.3)(V_{CC})$, $V_{IH} = (0.7)(V_{CC})$
- Quiescent Supply Current 10μA (Max)

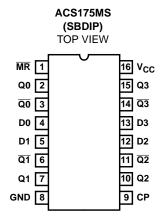
Applications

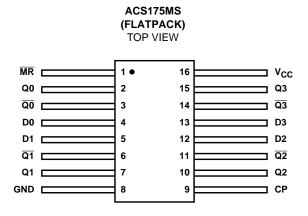
- High Speed Control Circuits
- Sensor Monitoring
- · Low Power Designs

Ordering Information

ORDERING NUMBER	INTERNAL MARKETING NUMBER	TEMP. RANGE (°C)	PACKAGE	DESIGNATOR
5962F9863501VCC	ACS175DMSR-03	-55 to 125	16 Ld SBDIP	CDIP2-T16
ACS175D/SAMPLE-03	ACS175D/SAMPLE-03	25	16 Ld SBDIP	CDIP2-T16
5962F9863501VXC	ACS175KMSR-03	-55 to 125	16 Ld Flatpack	CDFP4-F16
ACS175K/SAMPLE-03	ACS175K/SAMPLE-03	25	16 Ld Flatpack	CDFP4-F16
5962F9863501V9A	ACS175HMSR-03	25	Die	NA

Pinouts





Die Characteristics

DIE DIMENSIONS:

Size: $2390\mu m \times 2390\mu m$ (94 mils x 94 mils) Thickness: $525\mu m \pm 25\mu m$ (20.6 mils ± 1 mil) Bond Pad: $110\mu m \times 110\mu m$ (4.3 x 4.3 mils)

METALLIZATION: AI

Metal 1 Thickness: 0.7μm ±0.1μm Metal 2 Thickness: 1.0μm ±0.1μm

SUBSTRATE POTENTIAL

Unbiased Insulator

PASSIVATION:

Type: Phosphorous Silicon Glass (PSG)

Thickness: $1.30\mu m \pm 0.15\mu m$

SPECIAL INSTRUCTIONS

Bond V_{CC} First

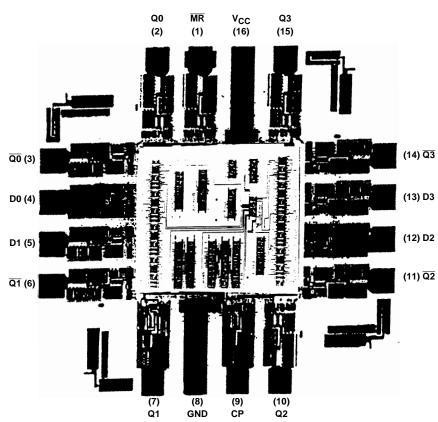
ADDITIONAL INFORMATION:

Worst Case Current Density: <2.0 x 10⁵ A/cm²

Transistor Count: 280

Metallization Mask Layout

ACS175MS



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